# Plastic High Power Silicon PNP Transistor

 $\dots$  designed for use up to 30 Watt audio amplifiers utilizing complementary or quasi complementary circuits.

- DC Current Gain hFE = 40 (Min) @ IC = 1.0 Adc
- BD802 is complementary with BD 795, 797, 799, 801

#### **MAXIMUM RATINGS**

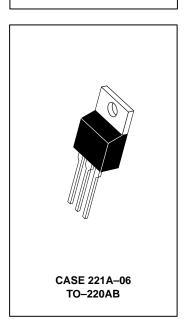
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	100	Vdc
Collector-Base Voltage	VCBO	100	Vdc
Emitter–Base Voltage	VEBO	5.0	Vdc
Collector Current	IC	8.0	Adc
Base Current	ΙΒ	3.0	Adc
Total Device Dissipation T <sub>C</sub> = 25°C Derate above 25°C	PD	65 522	Watts mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θJC	1.92	°C/W

## **BD802**

8 AMPERE
POWER TRANSISTORS
PNP SILICON
100 VOLTS
65 WATTS

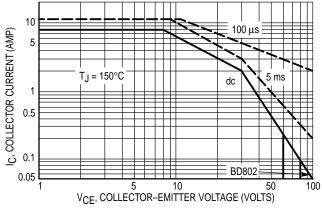


#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Sustaining Voltage* (IC = 0.05 Adc, I <sub>B</sub> = 0)	BVCEO	100	_	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 100 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	_	0.1	mAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	_	1.0	mAdc
DC Current Gain (I <sub>C</sub> = 1.0 A, V <sub>CE</sub> = 2.0 V) (I <sub>C</sub> = 3.0 A, V <sub>CE</sub> = 2.0 V)	hFE	30 15		
Collector–Emitter Saturation Voltage* (I <sub>C</sub> = 3.0 Adc, I <sub>B</sub> = 0.3 Adc)	VCE(sat)	_	1.0	Vdc
Base–Emitter On Voltage* (I <sub>C</sub> = 3.0 Adc, V <sub>CE</sub> = 2.0 Vdc)	VBE(on)	_	1.6	Vdc
Current–Gain — Bandwidth Product (I <sub>C</sub> = 0.25 Adc, V <sub>CE</sub> = 10 Vdc, f = MHz)	fΤ	3.0	_	MHz

<sup>\*</sup> Pulse Test: Pulse Width  $\leq 300 \,\mu\text{s}$ , Duty Cycle  $\leq 2.0$ .

#### **BD802**



The Safe Operating Area Curves indicate  $I_C - V_{CE}$  limits below which the device will not enter secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a catastrophic failure. To insure operation below the maximum  $T_J$ , power–temperature derating must be observed for both steady state and pulse power conditions.

Figure 1. Active Region Safe Operating Area

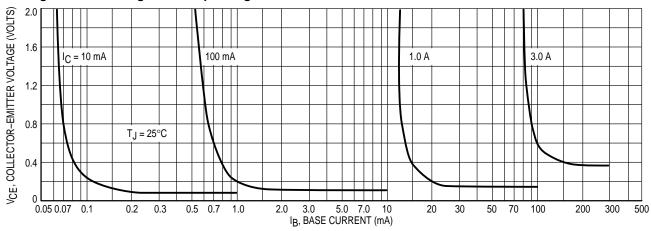
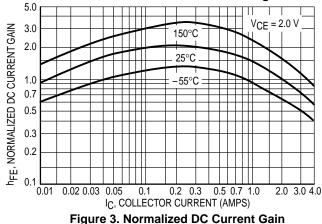
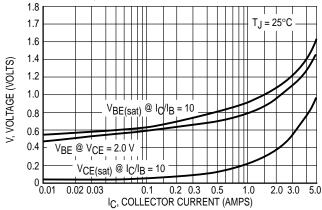
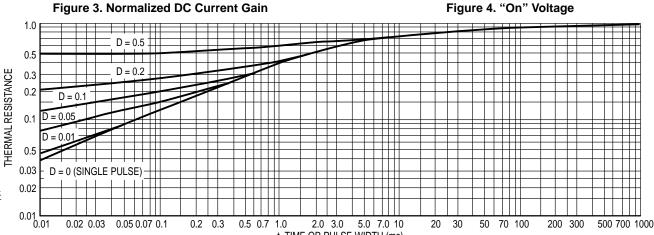


Figure 2. Collector Saturation Region



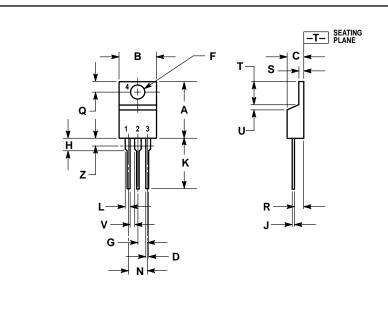




t, TIME OR PULSE WIDTH (ms)
Figure 5. Thermal Response

r(t), NORMALIZED EFFECTIVE TRANSIENT

### **PACKAGE DIMENSIONS**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
J	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

**CASE 221A-06** TO-220AB **ISSUE Y** 

#### **BD802**

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